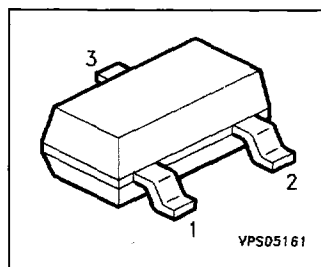


NPN Silicon RF Transistor

- For low noise, high-gain broadband amplifiers at collector currents from 1mA to 20mA
- $f_T = 8\text{GHz}$
 $F = 1.2\text{dB}$ at 900MHz



ESD: Electrostatic discharge sensitive device, observe handling precaution!

Type	Marking	Ordering Code	Pin Configuration			Package
BFR 182	RGs	Q62702-F1315	1 = B	2 = E	3 = C	SOT-23

Maximum Ratings

Parameter	Symbol	Values	Unit
Collector-emitter voltage	V_{CEO}	12	V
Collector-emitter voltage	V_{CES}	20	
Collector-base voltage	V_{CBO}	20	
Emitter-base voltage	V_{EBO}	2	
Collector current	I_C	35	mA
Base current	I_B	4	
Total power dissipation $T_S \leq 93^\circ\text{C}$	P_{tot}	250	mW
Junction temperature	T_j	150	
Ambient temperature	T_A	- 65 ... + 150	$^\circ\text{C}$
Storage temperature	T_{stg}	- 65 ... + 150	

Thermal Resistance

Junction - soldering point ¹⁾	R_{thJS}	≤ 230	K/W
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1) T_S is measured on the collector lead at the soldering point to the pcb.

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

DC Characteristics

Collector-emitter breakdown voltage $I_C = 1\text{ mA}$, $I_B = 0$	$V_{(BR)CEO}$	12	-	-	V
Collector-emitter cutoff current $V_{CE} = 20\text{ V}$, $V_{BE} = 0$	I_{CES}	-	-	100	μA
Collector-base cutoff current $V_{CB} = 10\text{ V}$, $I_E = 0$	I_{CBO}	-	-	100	nA
Emitter-base cutoff current $V_{EB} = 1\text{ V}$, $I_C = 0$	I_{EBO}	-	-	1	μA
DC current gain $I_C = 10\text{ mA}$, $V_{CE} = 8\text{ V}$	h_{FE}	50	100	200	-

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

AC Characteristics

Transition frequency $I_C = 15\text{ mA}$, $V_{CE} = 8\text{ V}$, $f = 500\text{ MHz}$	f_T	6	8	-	GHz
Collector-base capacitance $V_{CB} = 10\text{ V}$, $V_{BE} = v_{be} = 0$, $f = 1\text{ MHz}$	C_{cb}	-	0.33	0.5	pF
Collector-emitter capacitance $V_{CE} = 10\text{ V}$, $V_{BE} = v_{be} = 0$, $f = 1\text{ MHz}$	C_{ce}	-	0.2	-	
Emitter-base capacitance $V_{EB} = 0.5\text{ V}$, $V_{CB} = v_{cb} = 0$, $f = 1\text{ MHz}$	C_{eb}	-	0.6	-	
Noise figure $I_C = 3\text{ mA}$, $V_{CE} = 8\text{ V}$, $Z_S = Z_{Sopt}$ $f = 900\text{ MHz}$ $f = 1.8\text{ GHz}$	F	- -	1.2 1.9	- -	dB
Power gain ²⁾ $I_C = 10\text{ mA}$, $V_{CE} = 8\text{ V}$, $Z_S = Z_{Sopt}$ $Z_L = Z_{Lopt}$ $f = 900\text{ MHz}$ $f = 1.8\text{ GHz}$	G_{ma}	- -	17.5 11.5	- -	
Transducer gain $I_C = 10\text{ mA}$, $V_{CE} = 8\text{ V}$, $Z_S = Z_L = 50\ \Omega$ $f = 900\text{ MHz}$ $f = 1.8\text{ GHz}$	$ S_{21e} ^2$	- -	14.5 9	- -	

2) $G_{ma} = |S_{21}/S_{12}| (k - (k^2 - 1)^{1/2})$

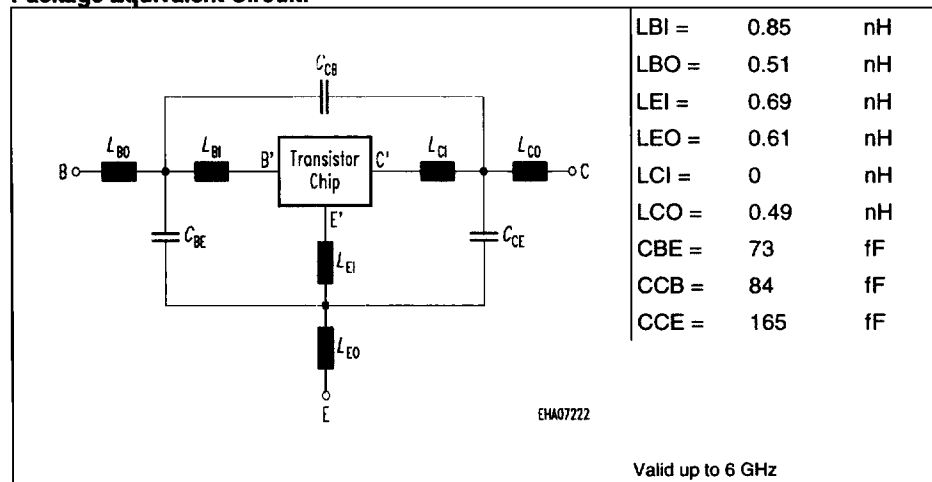
SPICE Parameters (Gummel-Poon Model, Berkeley-SPICE 2G.6 Syntax) :

Transistor Chip Data

IS =	4.8499	fA	BF =	84.113	-	NF =	0.56639	-
VAf =	21.742	V	IKF =	0.14414	A	ISE =	8.4254	fA
NE =	0.91624	-	BR =	10.004	-	NR =	0.54818	-
VAR =	2.2595	V	IKR =	0.03978	A	ISC =	5.9438	fA
NC =	0.5641	-	RB =	2.8263	Ω	IRB =	0.071955	mA
RBM =	3.4217	Ω	RE =	2.1858	Ω	RC =	1.8159	Ω
CJE =	8.8619	fF	VJE =	1.0378	V	MJE =	0.40796	-
TF =	22.72	ps	XTF =	0.43147	-	VTF =	0.34608	V
ITF =	6.5523	mA	PTF =	0	deg	CJC =	490.25	fF
VJC =	1.0132	V	MJC =	0.31068	-	XCJC =	0.19281	-
TR =	1.7541	ns	CJS =	0	fF	VJS =	0.75	V
MJS =	0	-	XTB =	0	-	EG =	1.11	eV
XTI =	3	-	FC =	0.64175	-	TNOM	300	K

All parameters are ready to use, no scaling is necessary.
 Extracted on behalf of SIEMENS Small Signal Semiconductors by:
 Institut für Mobil- und Satellitenfunktechnik (IMST)
 © 1996 SIEMENS AG

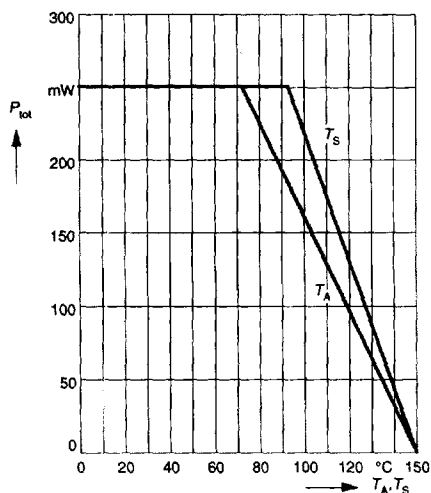
Package Equivalent Circuit:



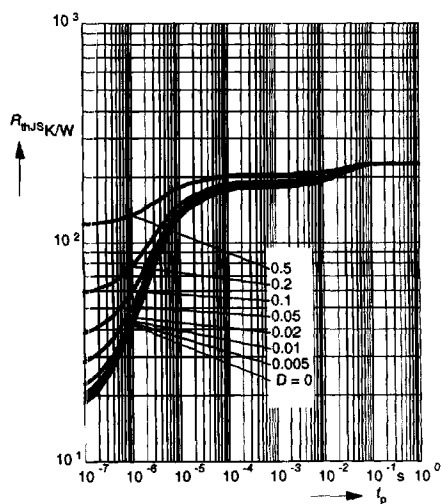
For examples and ready to use parameters please contact your local Siemens distributor or sales office to obtain a Siemens CD-ROM or see Internet: <http://www.siemens.de/Semiconductor/products/35/357.htm>

Total power dissipation $P_{\text{tot}} = f(T_A^*, T_S)$

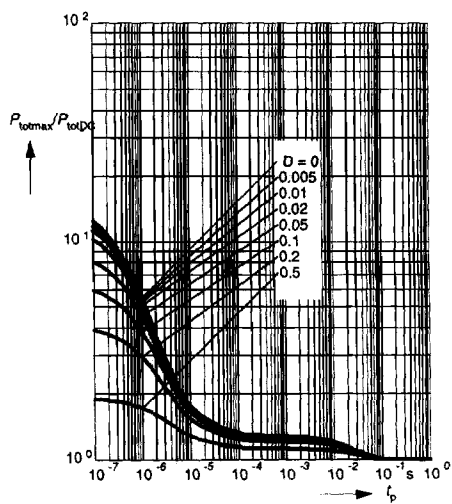
* Package mounted on epoxy



Permissible Pulse Load $R_{\text{thJS}} = f(t_p)$

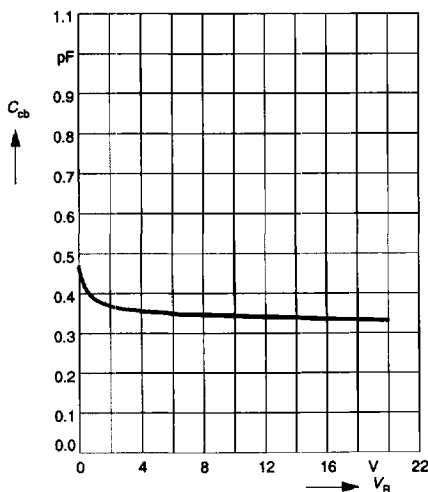


Permissible Pulse Load $P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$



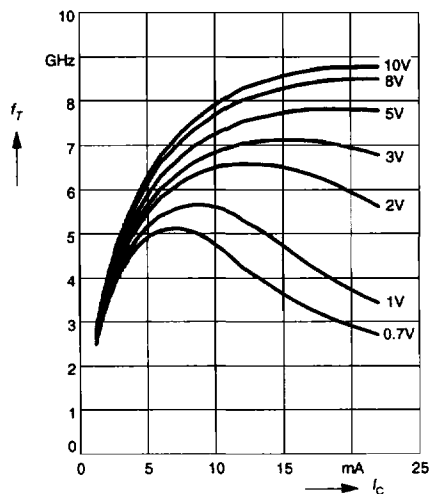
Collector-base capacitance $C_{cb} = f(V_{CB})$

$V_{BE} = V_{be} = 0, f = 1\text{MHz}$



Transition frequency $f_T = f(I_C)$

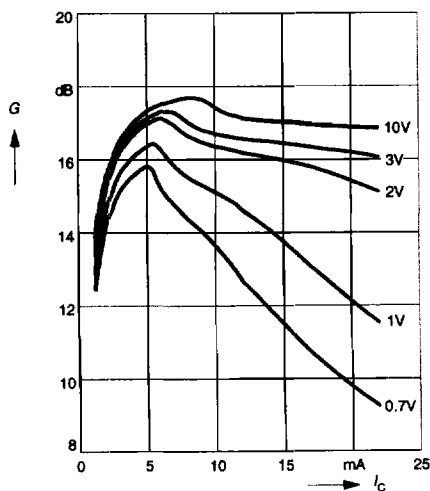
$V_{CE} = \text{Parameter}$



Power Gain $G_{ma}, G_{ms} = f(I_C)$

$f = 0.9\text{GHz}$

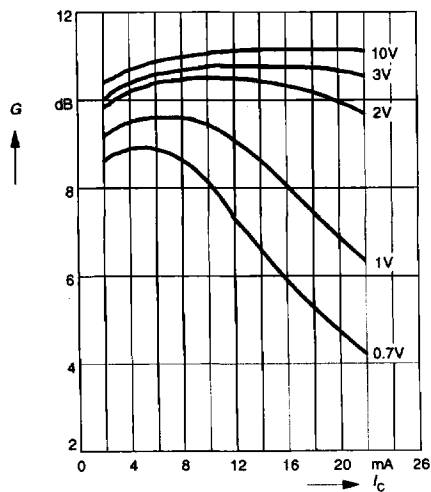
$V_{CE} = \text{Parameter}$



Power Gain $G_{ma}, G_{ms} = f(I_C)$

$f = 1.8\text{GHz}$

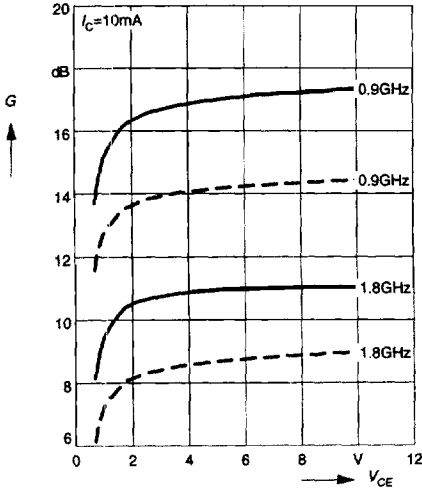
$V_{CE} = \text{Parameter}$



Power Gain $G_{ma}, G_{ms} = f(V_{CE})$: _____

$|S_{21}|^2 = f(V_{CE})$: -----

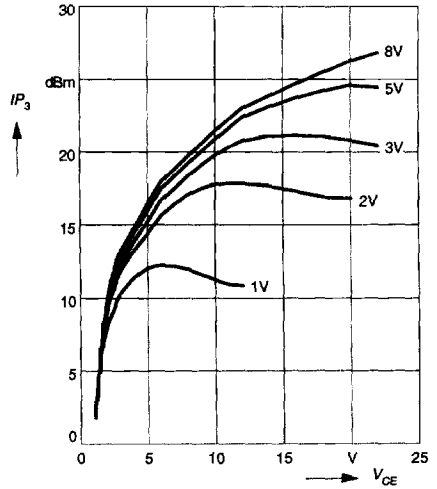
$f = \text{Parameter}$



Intermodulation Intercept Point $IP_3 = f(I_C)$

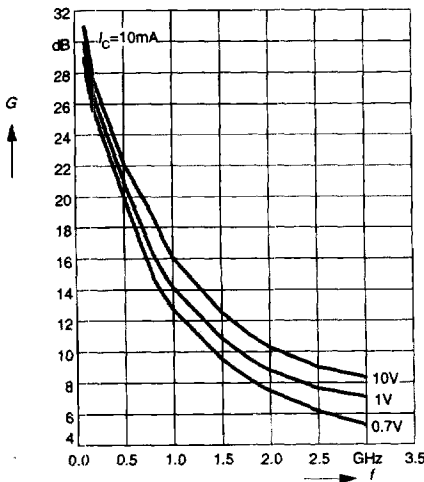
(3rd order, Output, $Z_S = Z_L = 50 \Omega$)

$V_{CE} = \text{Parameter}, f = 900 \text{ MHz}$



Power Gain $G_{ma}, G_{ms} = f(f)$

$V_{CE} = \text{Parameter}$



Power Gain $|S_{21}|^2 = f(f)$

$V_{CE} = \text{Parameter}$

